



Shantou Huashan Electronic Devices Co.,Ltd.

PNP SILICON TRANSISTOR

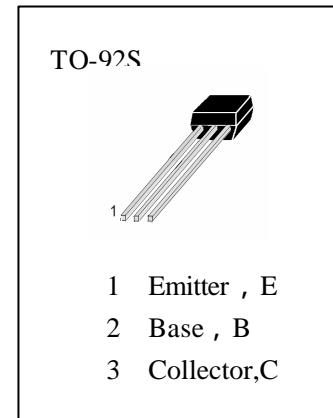
HX3906

APPLICATIONS

Small Signal Amplifier ; High Frequency oscillator ; Switching Applications .
(complement To H3904)

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ C$)

T_{stg} —Storage Temperature.....	-55~150
T_j —Junction Temperature.....	150
P_c —Collector Dissipation.....	300mW
V_{CBO} —Collector-Base Voltage.....	-40V
V_{CEO} —Collector-Emitter Voltage.....	-40V
V_{EBO} —Emitter-Base Voltage.....	-5V
I_c —Collector Current.....	-200mA



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CBO}	Collector-Base Breakdown Voltage	-40			V	$I_c=-100 \mu A, I_E=0$
BV_{CEO}	Collector-Emitter Breakdown Voltage	-40			V	$I_c=-10mA, I_B=0$
BV_{EBO}	Emitter- Base Breakdown Voltage	-5			V	$I_E=-10 \mu A, I_C=0$
I_{CBO}	Collector Cut-off Current			-0.1	μA	$V_{CB}=-30V, I_E=0$
I_{EBO}	Emitter Cut-off Current			-0.1	μA	$V_{EB}=-5V, I_C=0$
HFE	DC Current Gain	70		350		$V_{CE}=-1V, I_c=-10mA$
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage			-0.25	V	$I_c=-10mA, I_B=-1mA$
$V_{BE(sat)}$	Base- Emitter Saturation Voltage			-0.85	V	$I_c=-10mA, I_B=-1mA$
f_T	Current Gain-Bandwidth Product	300			MHz	$V_{CE}=-20V, I_c=-10mA$ $f=100MHz$

hFE Classification

A

B

70—240

220—350